Lecture 4. Homogeneously disordered SC films and S-N arrays

Plan of the Lecture

- 1) Suppression of T_c by disorder-enhanced Coulomb
 - 2) Mesoscopic fluctuations of T_c near the QPT
- 3) Quantum S-M transition: SC islands on top of a poor metal film
 - 4) Experimental realization: graphen
 - 5) Open field: Coulomb effects at T << Tc

1) Suppression of T_c in amorphous thin films by disorder-enhanced Coulomb interaction

Theory

- S. Maekawa and H. Fukuyama, J. Phys. Soc. Jpn. 51, 1380 (1982).
- H. Takagi and Y. Kuroda, Solid Stat. Comm. 41, 643 (1982).
- A. M. Finkel'stein, Pis'ma ZhETF 45, 37 (1987), [JETP Lett 45, 46 (1987)]; A. M. Finkel'stein in Proc. Int. Symp. on Anderson Localization, edited by T. Ando and H. Fukuyama (Springer-Verlag, Berlin, 1988), p. 230, Springer Proc. in Physics Vol. 28.

Experiment

- J. M. Graybeal and M. R. Beasly, Phys. Rev. B 29, 4167 (1984), J. M. Graybeal, M. R. Beasly, and R. L. Green, Physica B+C 126 731 (1984).
- P. Xiong, A. V. Herzog, and R. C. Dynes, Phys. Rev. Lett. 78, 927 (1997).

Review: A. M. Finkel'stein, Physica B **197**, 636 (1994).

Generalization to quasi-1D stripes:

Yu. Oreg and A. M. Finkel'stein

Phys. Rev. Lett. 83, 191 (1999)

Similar approach for 3D poor conductor near Anderson transition:

P. W. Anderson, K. A. Muttalib, and T. V. Ramakrishnan,

Phys. Rev. B **28**, 117 (1983)

Amorphous v/s Granular films

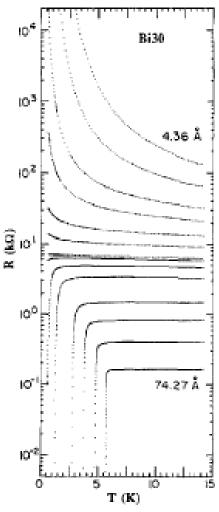


Fig. 5. Temperature dependence of the sheet resistance R(T) for Bi films deposited onto Ge [15]. The films are considered to be homogeneous.

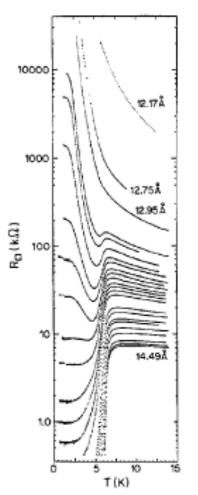


Fig. 6. Evolution of the resistive transition $R_{\square}(T)$ for granular Ga films [16].

Suppression of T_c in amorphous thin films: experimental data and fits to theory

J.Graybeal and M.Beasley

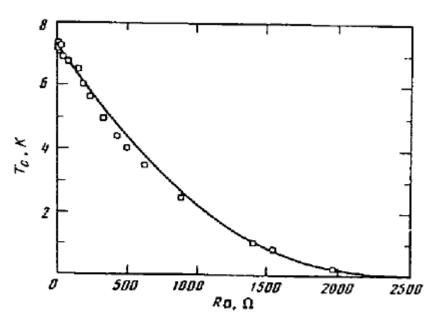


Fig. 14. Suppression of superconductivity in amorphous $Mo_{79}Ge_{21}$ [42]. The solid line is a theoretical fit with Eq. (13).

P. Xiong, A. V. Herzog, and R. C. Dynes,

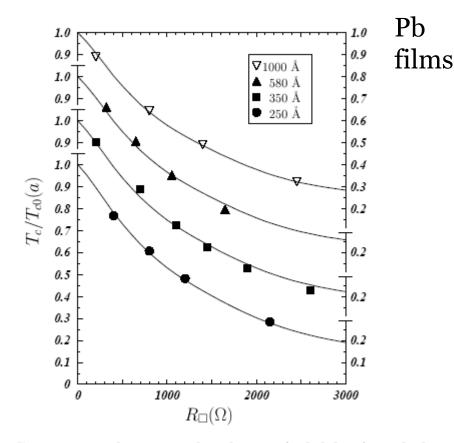


FIG. 3 Comparison between the theory (solid line) and the experimental data [13] for wires of different width. The short

Suppression of T_c in amorphous thin films: qualitative picture

• Disorder increases Coulomb interaction and thus decreases the pairing interaction (sum of Coulomb and phonon attraction). In perturbation theory:

$$\lambda(\varepsilon) = \lambda_0 - \frac{1}{24\pi g} Log\left(\frac{1}{\varepsilon\tau}\right)$$
 Return probability in 2D

Roughly,
$$\frac{\delta T_c}{T_c} = -\frac{\delta \lambda}{\lambda^2}$$
 Bu

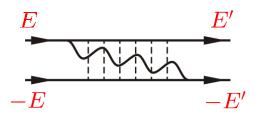
But in fact BCS-type problem with <u>energy-dependent</u> coupling must be solved

The origin of the correction term: ???????

Coulomb + disorder in 2D superconducting films

Finkelstein (1987)

Coulomb correction to the Cooper channel at $E < \tau^{-1}$:



$$\delta \lambda \sim \frac{1}{\nu} \int \frac{d\mathbf{q}}{Dq^2 + |E+E'|} \sim \frac{1}{g} \ln \frac{1}{|E+E'|\tau}$$

RG equation for $\lambda(E)$:

$$\frac{\partial \lambda}{\partial \zeta} = -\lambda^2 + \frac{1}{2\pi g}$$

$$\zeta = \ln \frac{1}{E\tau} \qquad g = \frac{h}{e^2 R_{\square}} \gg 1$$

 $\lambda(E)$ λ_g 0 $-\lambda_g$ $\zeta = \ln \frac{1}{E\tau}$

fixed points: $\pm \lambda_g$

$$\lambda_g = \frac{1}{\sqrt{2\pi g}}$$

$$\lambda(\zeta) = \frac{\lambda_0 + \lambda_g \tanh \lambda_g \zeta}{1 + \frac{\lambda_0}{\lambda_g} \tanh \lambda_g \zeta}$$

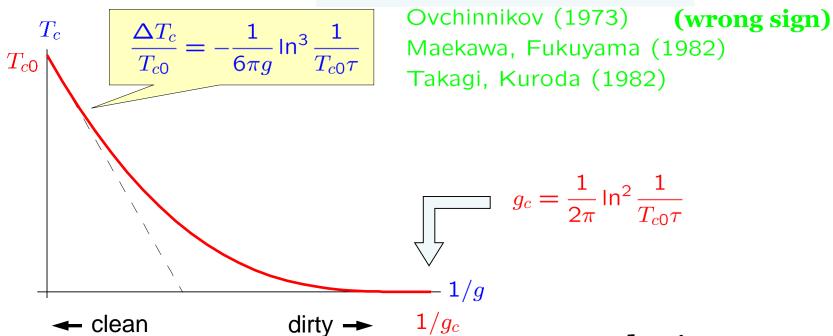
Coulomb suppression of T_c

Critical temperature

$$\frac{1}{|\lambda_0|} = \frac{1}{\lambda_g} \tanh(\lambda_g \zeta_c) \quad \Box$$

$$\frac{1}{|\lambda_0|} = \frac{1}{\lambda_g} \tanh(\lambda_g \zeta_c) \qquad \qquad T_c \tau = \left(\frac{1 - \frac{1}{\sqrt{2\pi g}} \ln \frac{1}{T_{c0} \tau}}{1 + \frac{1}{\sqrt{2\pi g}} \ln \frac{1}{T_{c0} \tau}}\right)^{\sqrt{\pi g/2}}$$

Finkelstein (1987)



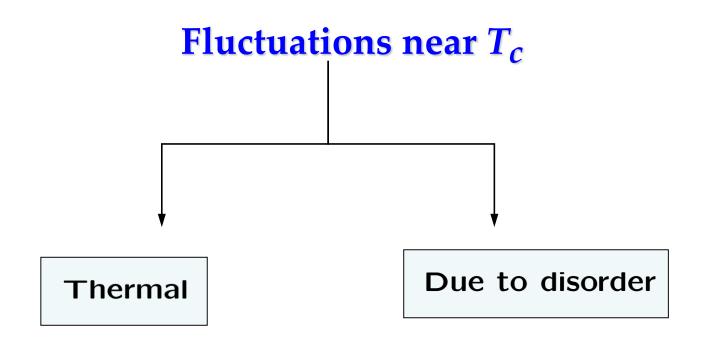
Conclusion:

At $\ln(1/T_{co}\tau) > 5$ $g_c > 4$ i.e. $R_c < R_O$



Superconductor – Metal Quantum phase transition

2) Mesoscopic fluctuations of T_c near the Finkelstein's Quantum Phase Transition



Thermal fluctuations: disorder and dimensionality

Ginzburg number

film of thickness d:

wire of area S:

dimensionless sheet conductance

$$R_O = 25 \,\mathrm{k}\Omega$$

Fluctuations due to disorder

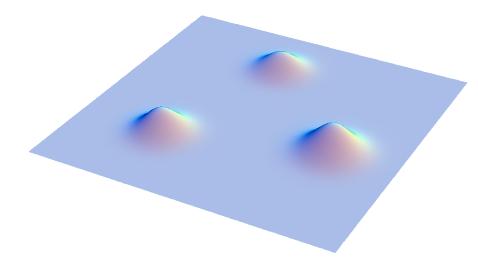
Linearized gap equation:
$$\Delta(\mathbf{r}) = \lambda \int K(\mathbf{r}, \mathbf{r}') \, \Delta(\mathbf{r}') \, d\mathbf{r}'$$
 disorder dependent!

Mean field

$$\langle \Delta(\mathbf{r}) \rangle = \lambda \int \langle K(\mathbf{r} - \mathbf{r}') \rangle \langle \Delta(\mathbf{r}') \rangle d\mathbf{r}'$$

Uniform solutions: $\Delta(\mathbf{r}) = \text{const}$

• Exact solution: localized superconducting droplets at $T > T_c^{\sf MF}$.



mesoscopic disorder at T=0, $H\to H_{c2}(0)$:

Spivak, Zhou (1995)
Galitski, Larkin (2001)
$$\frac{\delta I}{\overline{H}}$$

The goal:

To study mesoscopic fluctuation near the Coulomb-suppressed T_c

Way to go:

- 1) Derive the Ginzburg-Landau expansion
- 2) Include mesoscopic fluctuations of K(r,r')
- 3) Droplets of superconductive phase above T_c

Ginzburg-Landau expansion: step 1

$$F = \frac{\nu}{|\lambda_0|} \int d\mathbf{r} \, \Delta^*(\mathbf{r}) \Delta(\mathbf{r}) - \int d\mathbf{r} \, d\mathbf{r}' \, \Delta^*(\mathbf{r}) \Delta(\mathbf{r}') K(\mathbf{r}, \mathbf{r}')$$

$$+ \frac{1}{2} \int d\mathbf{r}_1 d\mathbf{r}_2 d\mathbf{r}_3 d\mathbf{r}_4 \, \Delta^*(\mathbf{r}_1) \Delta(\mathbf{r}_2) \Delta^*(\mathbf{r}_3) \Delta(\mathbf{r}_4) K^{(4)}(\mathbf{r}_1, \mathbf{r}_2, \mathbf{r}_3, \mathbf{r}_4) + \dots$$

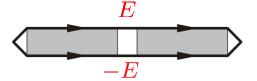
$$\langle K(\mathbf{q}) \rangle = \begin{array}{c|c} E & E' & E' \\ \hline -E & -E & -E' \\ \hline T \sum_{E} \frac{1}{|E|} & T^2 \sum_{E,E'} \frac{1}{|E|} \frac{1}{|E'|} \frac{1}{g} \ln \frac{1}{|E+E'|\tau} \\ \hline \int_{0}^{\zeta_{T}} d\zeta = \zeta_{T} & \frac{1}{g} \int_{0}^{\zeta_{T}} d\zeta \, d\zeta' \min(\zeta, \zeta') = \frac{\zeta_{T}^{3}}{3g} \end{array}$$

Uniform free energy:

$$F = \nu \int d\mathbf{r} \left(\frac{1}{|\lambda_0|} - \frac{1}{\lambda_g} \tanh(\lambda_g \zeta_T) \right) |\Delta(\mathbf{r})|^2 \implies \nu (T/T_c - 1) \int d\mathbf{r} \frac{|\Delta(\mathbf{r})|^2}{\cosh^2(\lambda_g \zeta_c)}$$

Ginzburg-Landau expansion: step 2

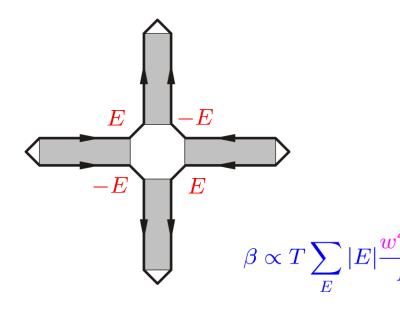
• Gradient term:



$$\left. \frac{\partial}{\partial Dq^2} \frac{1}{Dq^2 + 2|E|} \right|_{q=0} \sim \frac{1}{E^2}$$

$$\gamma \propto T \sum_{E} \frac{w^2(\zeta)}{E^2} \approx w^2(\zeta_T) T \sum_{E} \frac{1}{E^2}$$

• Quartic term:



Screening factor

$$\frac{w(E)}{|E|} = T \sum_{E'} \frac{E}{-E} \frac{E'}{-E'}$$

$$w(\zeta) = \cosh \lambda_g \zeta - \tanh \lambda_g \zeta_T \sinh \lambda_g \zeta$$

$$w(\zeta_T) = \frac{1}{\cosh \lambda_a \zeta_T}$$

$$\beta \propto T \sum_{E} |E| \frac{w^4(\zeta)}{E^4} \approx w^4(\zeta_T) T \sum_{E} \frac{1}{|E|^3}$$

Ginzburg-Landau expansion: result

$$F[\Delta] = \int \left[\alpha (T/T_c - 1) |\tilde{\Delta}|^2 + \gamma |\nabla \tilde{\Delta}|^2 + \frac{\beta}{2} |\tilde{\Delta}|^4 \right] d\mathbf{r}$$

 α , β and γ are the usual GL parameters for dirty superconductors, and

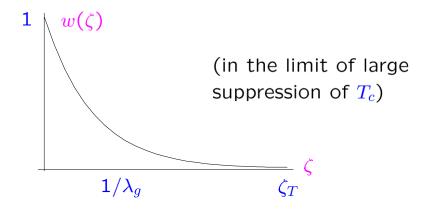
$$ilde{\Delta} = \Delta w(\zeta_{T_c}) = rac{\Delta}{\cosh \lambda_g \zeta_{T_c}} \qquad \qquad \left(\lambda_g = rac{1}{\sqrt{2\pi g}}, \; \; \zeta = \ln rac{1}{E au}
ight)$$

Gi is the same as in the absense of the Coulomb repulsion:

$$Gi = \frac{\pi}{8 q}$$

Physical meaning of \triangle

A quasiparticle propagating at energy E feels the pairing potential $\Delta w(\zeta)$



Mesoscopic fluctuations of the kernel K(r,r'): step 1

$$F^{(2)} = \int d\mathbf{r} \, d\mathbf{r}' \, \Delta^*(\mathbf{r}) \left(\frac{\nu \delta(\mathbf{r} - \mathbf{r}')}{|\lambda_0|} - K(\mathbf{r}, \mathbf{r}') \right) \Delta(\mathbf{r}')$$

$$\langle K(\mathbf{r} - \mathbf{r}') \rangle + \delta K(\mathbf{r}, \mathbf{r}')$$

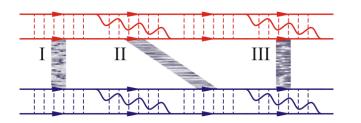
Length scales:

- $\langle \langle \delta K(\mathbf{r}_1, \mathbf{r}_2) \delta K(\mathbf{r}_3, \mathbf{r}_4) \rangle \rangle$: decays at $\mathbf{r}_i \mathbf{r}_j \sim L_T = \sqrt{D/T_c}$
- ullet superconductive coherence length $\xi(T) = L_T \sqrt{rac{T_c}{T-T_c}} \gg L_T$

From the viewpoint of the superconductive system, fluctuations of $K(\mathbf{r}, \mathbf{r}')$ are short-ranged and characterized by a single number:

$$C = \int \langle \langle \delta K(\mathbf{r}_1, \mathbf{r}_2) \delta K(\mathbf{r}_3, \mathbf{r}_4) \rangle \rangle d\mathbf{r}_2 d\mathbf{r}_3 d\mathbf{r}_4$$

Mesoscopic fluctuations of the kernel K(r,r'): step 2



*** Calculation was here ***

$$C = \frac{w_0^2(T)}{\pi D} \left(T^2 \sum_{\varepsilon, \varepsilon' > 0} \frac{1}{\varepsilon \varepsilon'(\varepsilon + \varepsilon')} \right) \left[w_0(T) + \frac{1}{g} T \sum_{\varepsilon > 0} \frac{w_0(\varepsilon)}{\varepsilon} \ln \frac{1}{\varepsilon \tau} \right]^2$$

$$1 - w_0(T)$$
mesoscopic fluctuations of return probability
$$C = \frac{7\zeta(3)}{8\pi^4 DT} \frac{1}{\cosh(\lambda_g \zeta_T)}$$
2 instead of 4!

Superconductor with fluctuating T_c

Superconductor with fluctuating T_c (Ioffe, Larkin (1981)): Sov.Phys.JETP **54**, 378 (1981)

$$F = \int \left\{ \left[\alpha (T/T_c - 1) + \delta \alpha(\mathbf{r}) \right] |\tilde{\Delta}|^2 + \gamma |\nabla \tilde{\Delta}|^2 + \frac{\beta}{2} |\tilde{\Delta}|^4 \right\} d\mathbf{r}$$

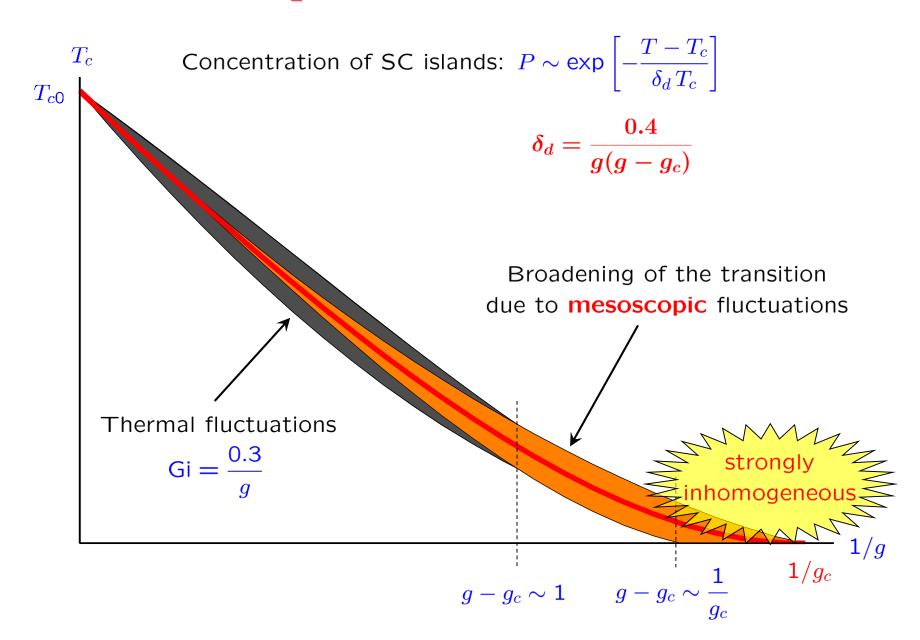
$$\langle \delta \alpha(\mathbf{r}) \delta \alpha(\mathbf{r}') \rangle = \frac{C}{w^4(T)} \delta(\mathbf{r} - \mathbf{r}') = \frac{7\zeta(3)}{8\pi^4 DT} \cosh^2(\lambda_g \zeta_T) \delta(\mathbf{r} - \mathbf{r}')$$

GL equation looks like a Schrödinger equation with random potential Zittartz, Langer; Halperin, Lax (1966)



Instantons

Mesoscopic vs. thermal fluctuations



Conclusion of the part 2):

Close to the quantum critical point, at $g-g_c \leq 1$, the superconducting phase transition is due to overlapping superconducting droplets created by mesoscopic fluctuations

3) Quantum S-M transition: SC islands on the top of a poor metal film

- M. V. Feigel'man and A. I. Larkin Chem. Phys. Lett. 235, 107 (1998)
- B. Spivak, A. Zyuzin, and M. Hruska
 Phys. Rev. B 64, 132502 (2001)
- M. V. Feigel'man, A. I. Larkin and M.A.Skvortsov Phys. Rev. Lett. **86**, 1869 (2001)

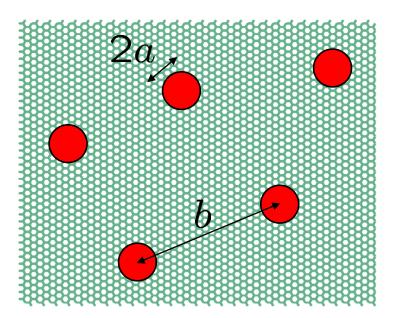
4) Experimental realization: graphen

Suggested in M. Feigel'man, M. Skvortsov and K. Tikhonov JETP Letters 88(11), 747-751 (2008); arXiv:0810.0109]

First experiment: <u>B.M. Kessler</u>, <u>C.O. Girit</u>, <u>A. Zettl</u>, <u>V. Bouchiat</u>

arxiv: 0907.3661_

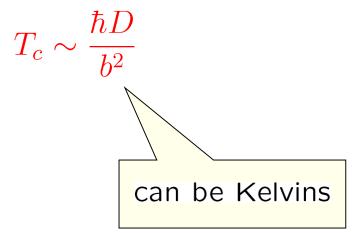
Graphene + superconducting islands



Graphene can be made superconductive if small superconductive islands are placed on top of it

disordered graphene

scales: $l \leq a \ll b$



Josephson coupling via disordered graphene

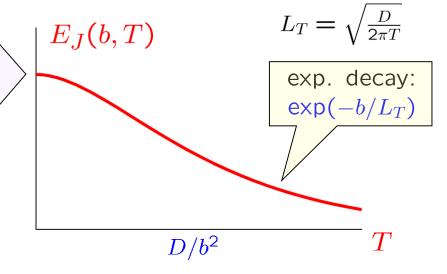
$$2a \uparrow \bigcirc b$$
 φ_1 φ_2

$$\mathcal{H} = -E_J(b, T)\cos(\varphi_1 - \varphi_2)$$

- Usadel equation (at l < r)
- linearization $(a \ll b)$: $F_E(\mathbf{r}) = F_E^{(\varphi_1)}(\mathbf{r} \mathbf{r}_1) + F_E^{(\varphi_2)}(\mathbf{r} \mathbf{r}_2)$

$$E_{J}(b,T) = 16\pi^{3}gT \sum_{\omega_{n}>0} \frac{P(\sqrt{\omega_{n}r^{2}/2D})}{\ln^{2}(\omega_{n}a^{2}/D)}, \quad P(z) = z \int_{0}^{\infty} K_{0}(z\cosh t)K_{1}(z\cosh t) dt$$

good contact $E_J(b,0) = \frac{\pi^3}{4} \frac{g}{\ln^2(b/a)} \frac{D}{b^2}$ tunnel barrier $G_T = E_J(b,0) = \frac{G_T^2}{8\pi a} \frac{D}{b^2}$



Thermal phase transition

JJ array:

XY model:

$$\mathcal{H} = -\sum_{ij} E_J(b, T) \cos(\varphi_i - \varphi_j) \qquad \qquad \mathcal{H} = \frac{\Upsilon(T)}{2} \int d\mathbf{r} \, (\nabla \varphi)^2$$

$$\mathcal{H} = \frac{\Upsilon(T)}{2} \int d\mathbf{r} (\nabla \varphi)^2$$

Superfluid stiffness:
$$\Upsilon(T) = \frac{c}{2b^2} \sum_{i} |\mathbf{r}_i - \mathbf{r}_j|^2 E_J(\mathbf{r}_i - \mathbf{r}_j, T)$$

The systems exhibits the **BKT** transition at $\Upsilon(T_c) = (2/\pi)T_c$

Josephson coupling is short-ranged

$$T_c = \gamma E_J(T_c)$$

$$E_{\mathsf{Th}} = \frac{D}{b^2}$$

at
$$T \sim T_c$$

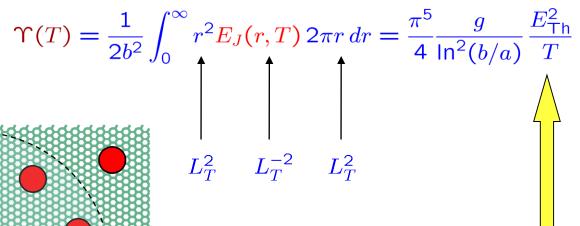
for triangular lattice $\gamma = 1.5$ (Shih and Stroud 1985)

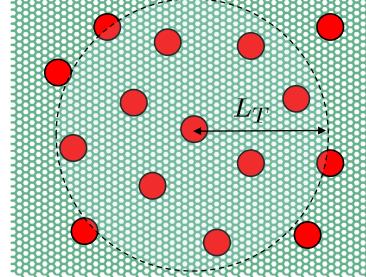
- at $T > T_c$, phases of different islands are uncorrelated
- at $T < T_c$, all phases phases look in the same direction

Superfluid density below T_c

At $T \ll T_c$, the Josephson coupling is long-ranged.

Many islands contribute to the superfluid stiffness $\Upsilon(T)$:





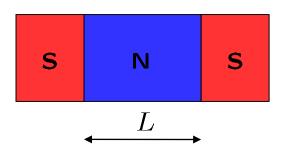
Strong divergence of $\Upsilon(T \to 0)$

Did we forget something?

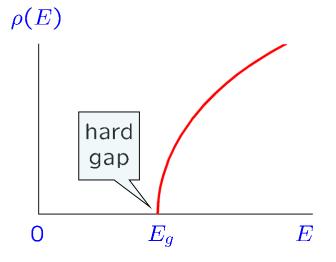


Spectral gap

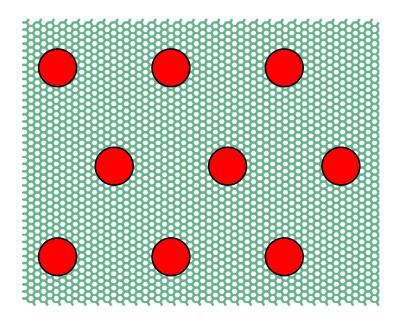
Minigap in an SNS junction



$$E_g \simeq 3.1 rac{D}{L^2}$$



Regularly placed islands on graphene



Numeric integration of the Usadel eq. gives

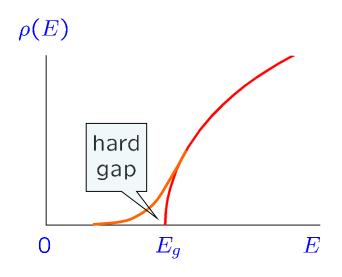
$$E_g \simeq rac{2.6}{\ln(b/a)} rac{D}{b^2}$$

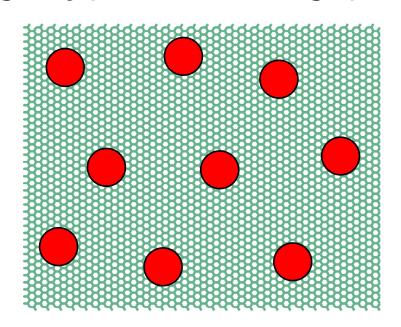
Can be seen in STM experiments

Spectral gap in an irregular system

Iregularly placed islands on graphene

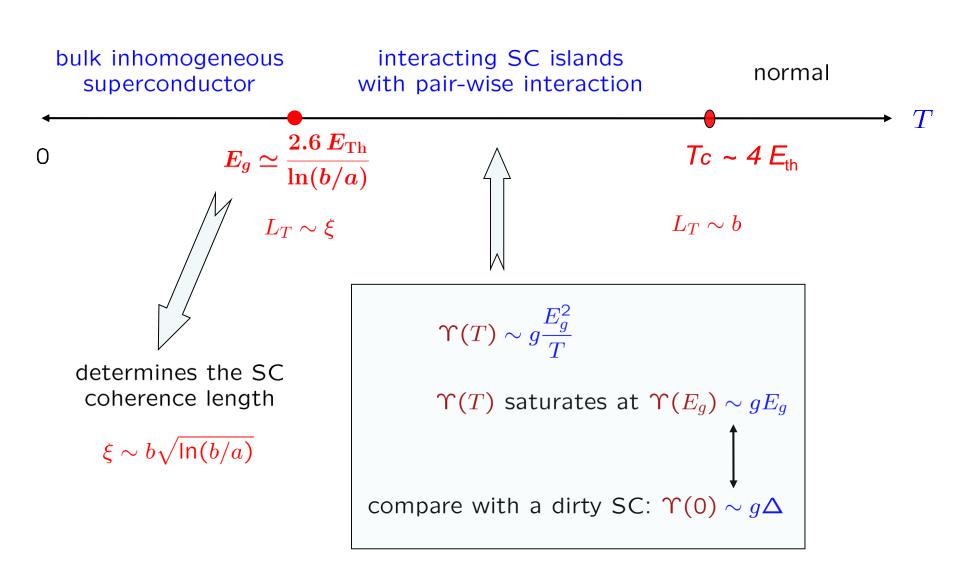
The hard gap will be smeared





The relative smearing is expected to be small:
$$rac{\delta E_g}{E_g} \sim rac{1}{\ln(b/a)}$$

Two-energy-scale superconductivity



Magnetic field effect (low *T*, low *H*)

Small H: like in a 2D superconductor with $\Delta \sim E_g$

Critical field:

$$H_g \simeq rac{c E_g}{e D} = rac{2.6}{\pi \ln b/a} rac{\Phi_0}{b^2}$$

$$H_g \sim 100 \; ext{G}$$
 at $b \sim 300 \; ext{nm}$

$$H < H_g$$

- disordered vortex lattice
- core size $\xi \sim b \ln(b/a) \gg b$
- strong pinning

$$H > H_g$$

- spectral gap is totally suppressed
- gapples SC ⇔ SC glass
- weakly frustrated

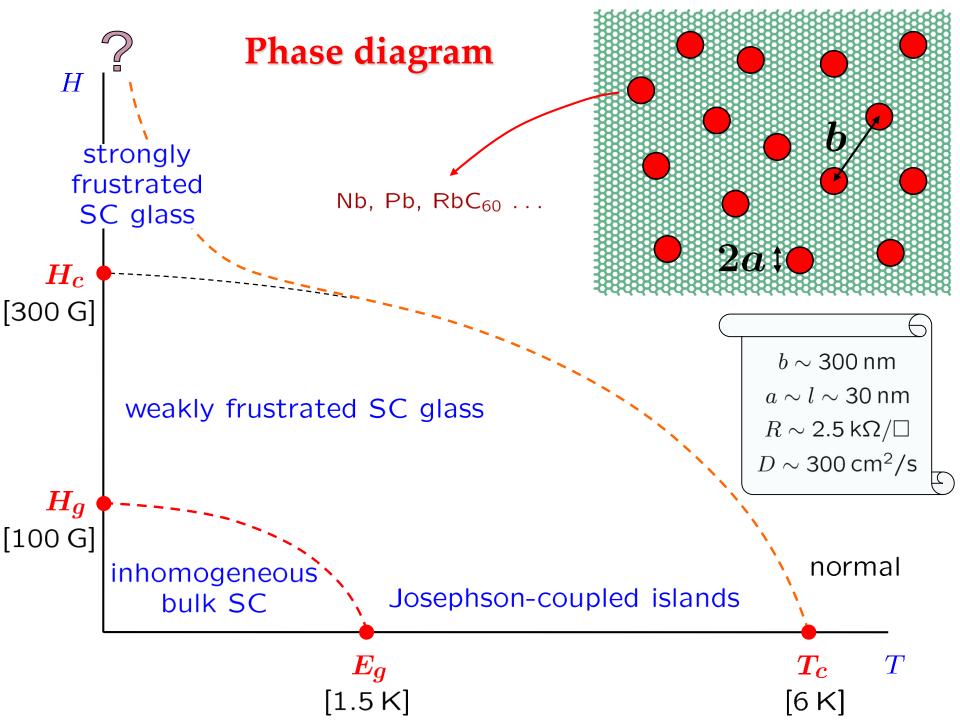
Magnetic field effect (low *T*, high *H*)

$$H_c \sim rac{\Phi_0}{b^2} \gg H_g$$

At $H \sim H_c$ the Josephson coupling bewteen the nearest islands becomes totally frustated

average coupling:
$$\langle E_J(r_{ij}) \rangle \sim g \frac{D}{r_{ij}^2} \exp(-r_{ij}/L_H)$$

mesoscopic fluctuations:
$$\sqrt{\langle E_J^2(r_{ij})\rangle} \sim \frac{D}{r_{ij}^2}$$



Conclusions for the theory in part 4)

- 1. Graphene can be made superconductive at Kelvins with very small part of area covered by superconductive islands
- 2. Spectral gap expected due to proximity effect should be measurable by low-temperature STM (and destroyed easily by magnetic field)
- 3. Transformation from continous disordered superconductor to weakly coupled junction's array is predicted with growth of either T or B
- 4. Approaching the neutrality point will lead to island's decoupling and T=0 quantum phase transition to metal

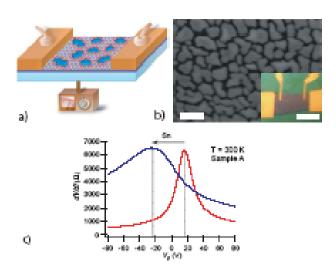


FIG. 1: (Color online) a) Schematic of device configuration and measurement setup. Blue islands correspond to Sn clusters. b) Scanning electron micrograph of Sn island morphology on the graphene sheet (Scale bar = 100 nm. Inset: optical image of a typical device showing the four probe configuration (Scale bar 10 microns) c) Four-terminal sheet resistance as a function of gate voltage for Sample A before (red online) and after (blue online) Sn deposition. The dotted lines indicate the charge neutral point and the arrow indicates the shift after Sn deposition.

New experiments are on the way: Bilayer graphen, STM probe, Low-fraction covering

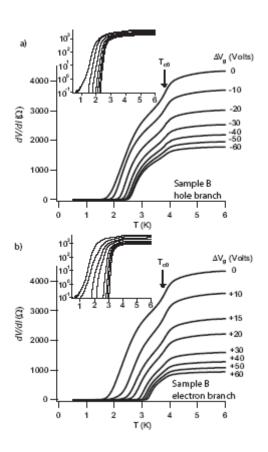


FIG. 2: Sheet resistance versus temperature for various gate voltages, V_g , referenced to the charge neutrality point $V_D=+40$ V for this device. In a) $\Delta V_g=V_g-V_D<0$ corresponds to hole transport, whereas, $\Delta V_g>0$ in b) corresponds to electron transport through the graphene sheet. The arrow labeled T_{c0} indicates the first partial resistance drop corresponding to the mean-field pairing transition of the Sn islands. Inset: Same data on a log scale.

5) Open problems

DoS smearing at low temperatures

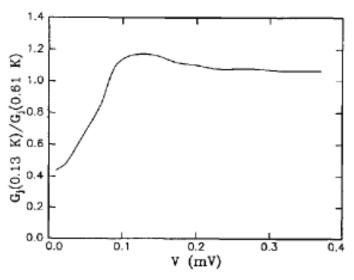


Fig. 16. Tunnel junction conductance of a $5.8 \,\mathrm{k}\Omega/_{\odot}$ Bi film at $T = 0.13 \,\mathrm{K}$ normalized to its conductance at $T = 0.61 \,\mathrm{K}$ [40].

Mesoscopic fluctuations of Hc2 at g near gc

$$[\delta H_{c2} / H_{c2} \sim 1/g$$
 at $g >> gc]$